

### General Description

The QM3006U1 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The QM3006U1 meet the RoHS and Halogen-free Product requirement, 100% EAS guaranteed with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Halogen - Free Device Available

### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	80	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	57	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	17	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	14.5	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	160	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	252	mJ
$I_{AS}$	Avalanche Current	48	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	53	W
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>4</sup>	2.4	W
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 175	$^\circ C$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	2.8	$^\circ C/W$

### Product Summary

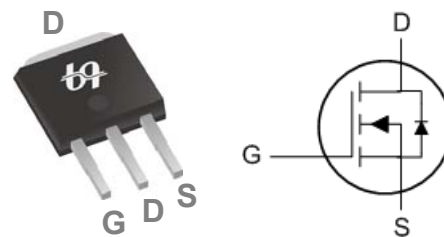
### Halogen-Free

BVDSS	RDSON	ID
30V	5.5m $\Omega$	80A

### Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

### TO251S Pin Configuration



### Electrical Characteristics ( $T_J=25\text{ }^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$	---	0.028	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=30A$	---	4.7	5.5	m $\Omega$
		$V_{GS}=4.5V, I_D=15A$	---	7.5	9	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-6.16	---	mV/ $^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=30V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
		$V_{DS}=30V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=30A$	---	43	---	S
$R_g$	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	1.7	2.7	$\Omega$
$Q_g$	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=4.5V, I_D=15A$	---	20	25	nC
$Q_{gs}$	Gate-Source Charge		---	7.6	9.5	
$Q_{gd}$	Gate-Drain Charge		---	7.2	9	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega, I_D=15A$	---	7.8	9.8	ns
$T_r$	Rise Time		---	15	18.8	
$T_{d(off)}$	Turn-Off Delay Time		---	37.3	47	
$T_f$	Fall Time		---	10.6	13.3	
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	2295	2755	pF
$C_{oss}$	Output Capacitance		---	267	320	
$C_{riss}$	Reverse Transfer Capacitance		---	210	252	

### Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	$V_{DD}=25V, L=0.1\text{mH}, I_{AS}=24A$	63	---	---	mJ

### Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,6</sup>	$V_G=V_D=0V$ , Force Current	---	---	80	A
$I_{SM}$	Pulsed Source Current <sup>2,6</sup>		---	---	160	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V
$t_{rr}$	Reverse Recovery Time	$I_F=30A, dI/dt=100A/\mu\text{s}$ ,	---	14	---	nS
$Q_{rr}$	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	5	---	nC

Note :

- The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- The data tested by pulsed, pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$
- The EAS data shows Max. rating. The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=48A$
- The power dissipation is limited by  $175^\circ\text{C}$  junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.

## N-Ch 30V Fast Switching MOSFETs

### Typical Characteristics

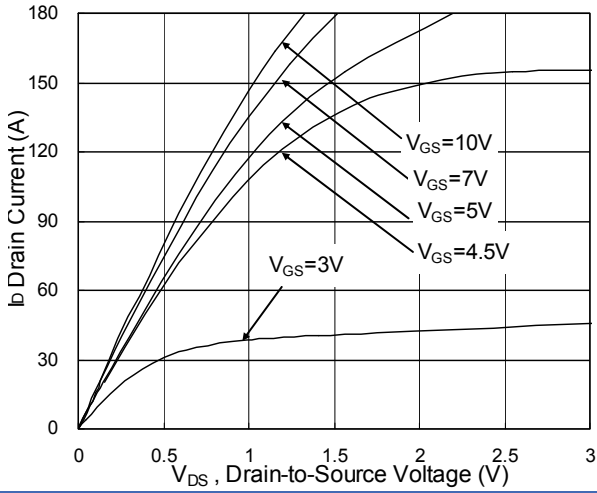


Fig.1 Typical Output Characteristics

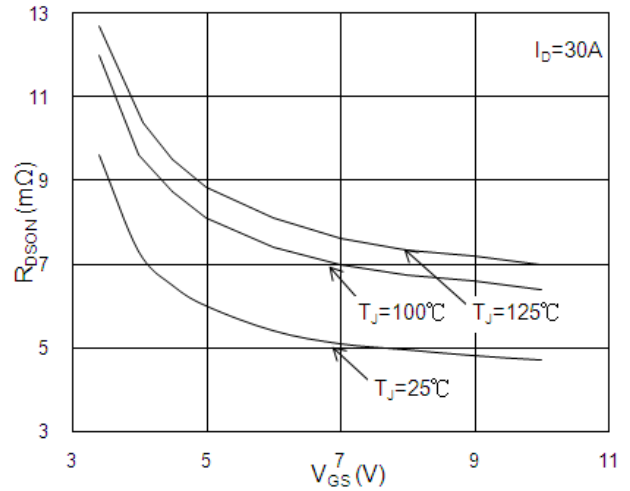


Fig.2 On-Resistance vs. G-S Voltage

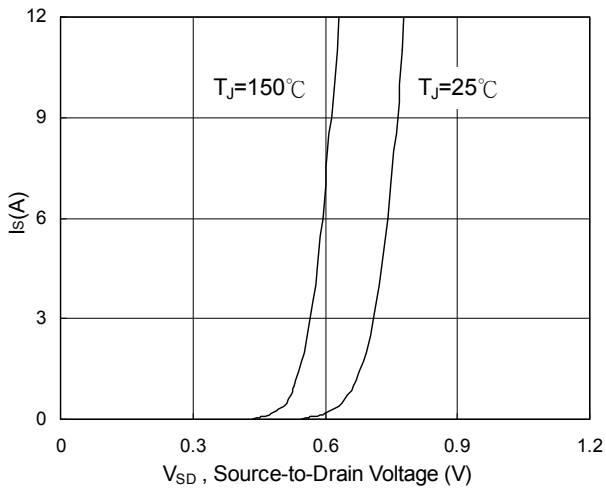


Fig.3 Forward Characteristics of Reverse

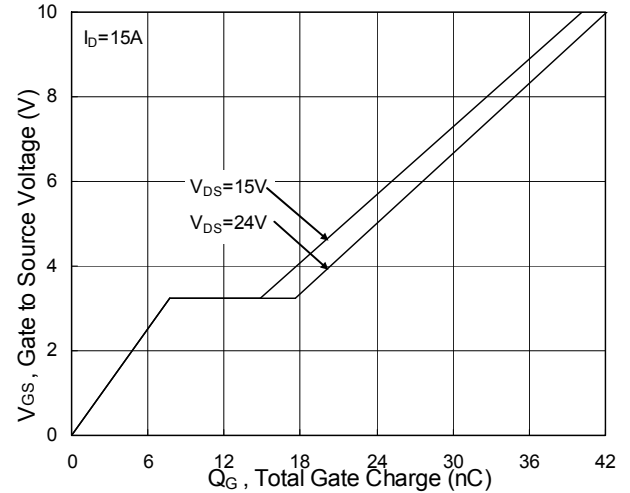


Fig.4 Gate-Charge Characteristics

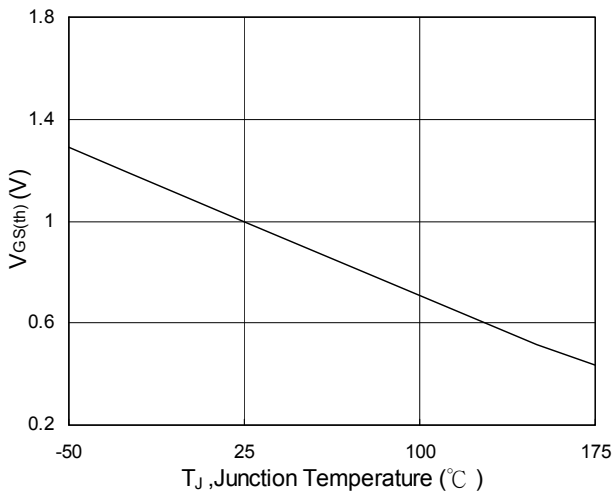


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

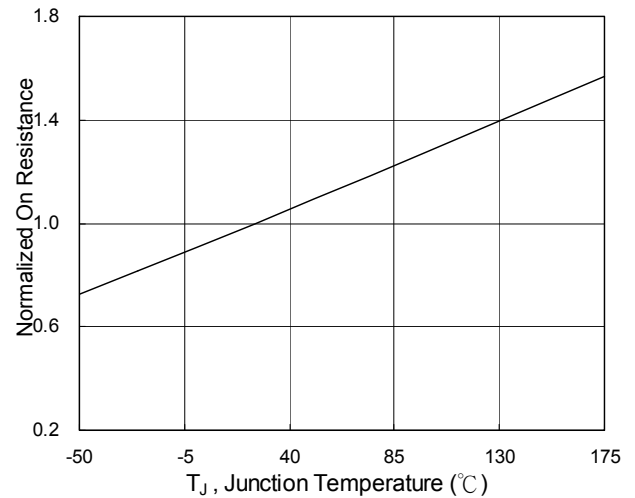
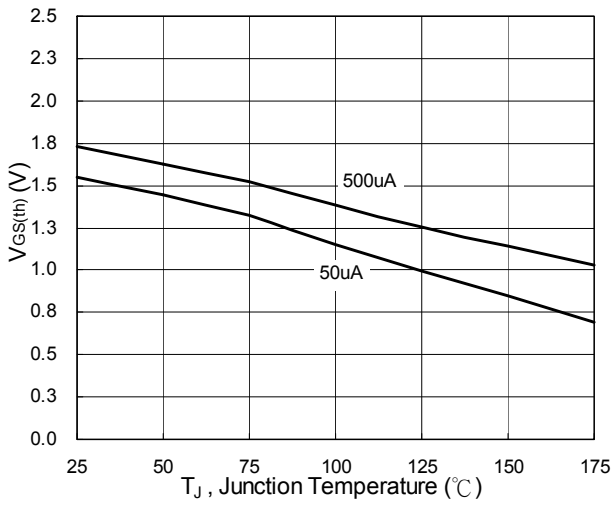
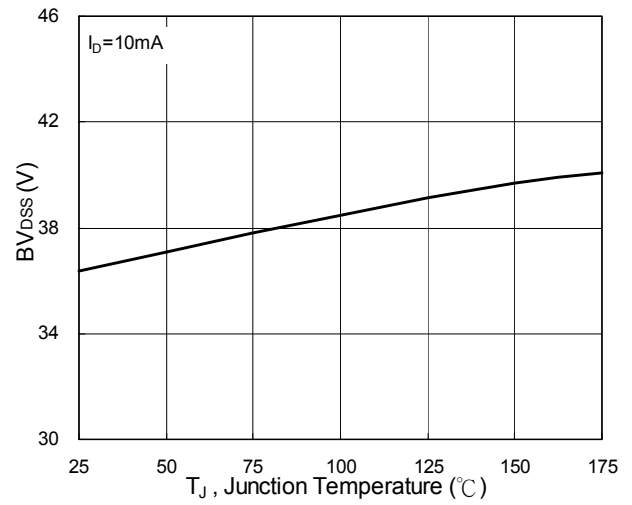


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

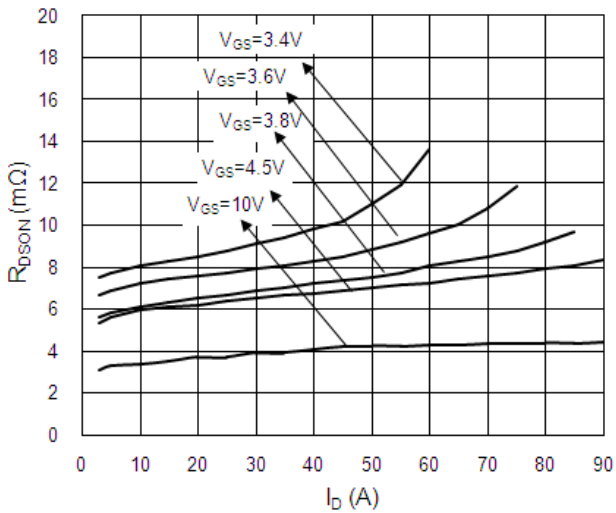
## N-Ch 30V Fast Switching MOSFETs



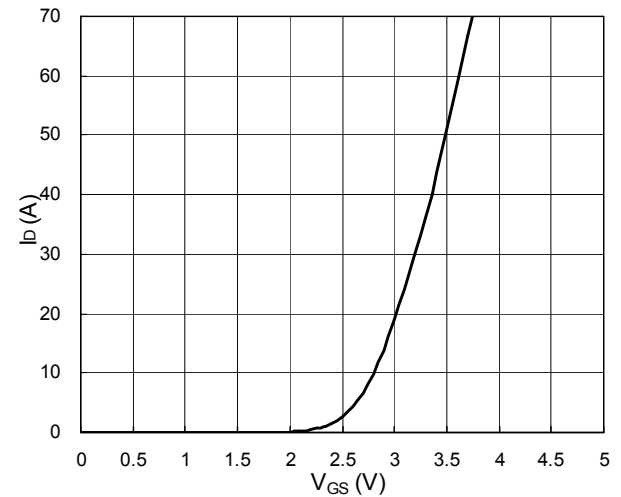
**Fig.7  $V_{GS(th)}$  vs.  $T_J$**



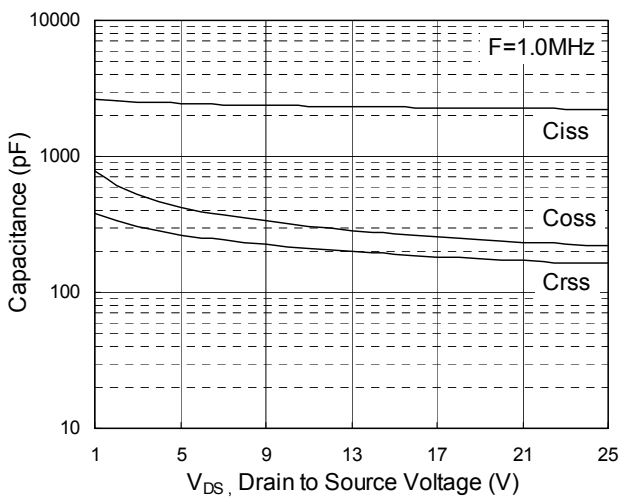
**Fig.8  $B_{VDSS}$  vs.  $T_J$**



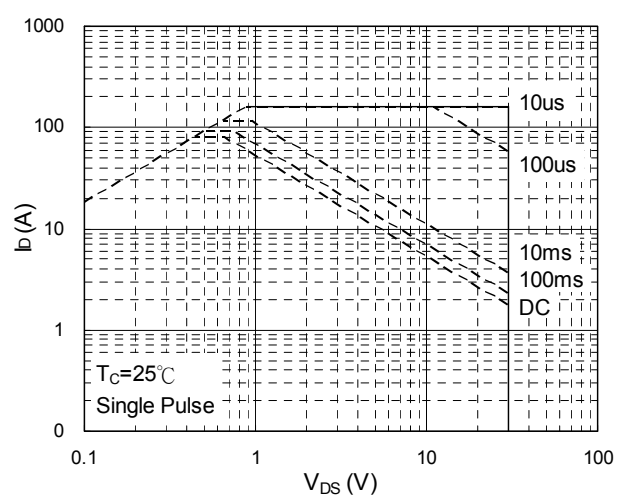
**Fig.9 On-Resistance vs. Drain Current**



**Fig.10 Transfer Characteristics**



**Fig.11 Capacitance**



**Fig.12 Safe Operating Area**

## N-Ch 30V Fast Switching MOSFETs

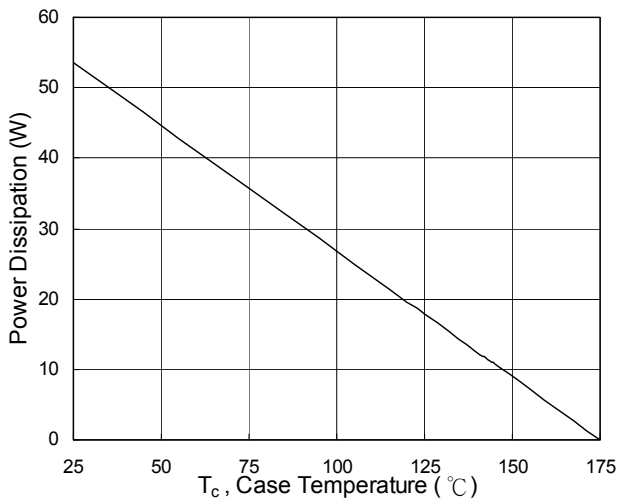


Fig.13 Power Derating

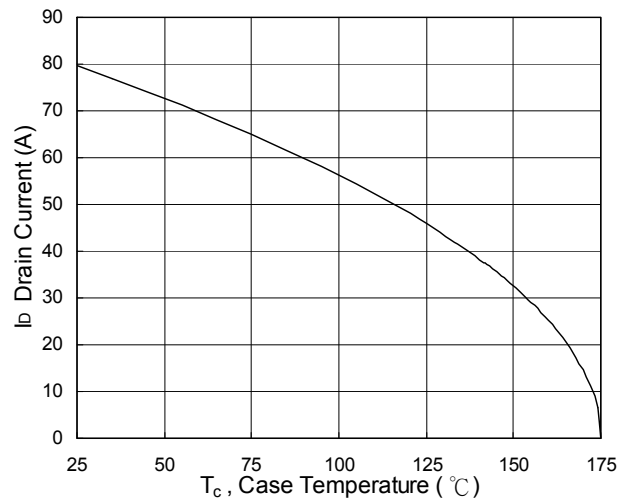


Fig.14 Current Derating

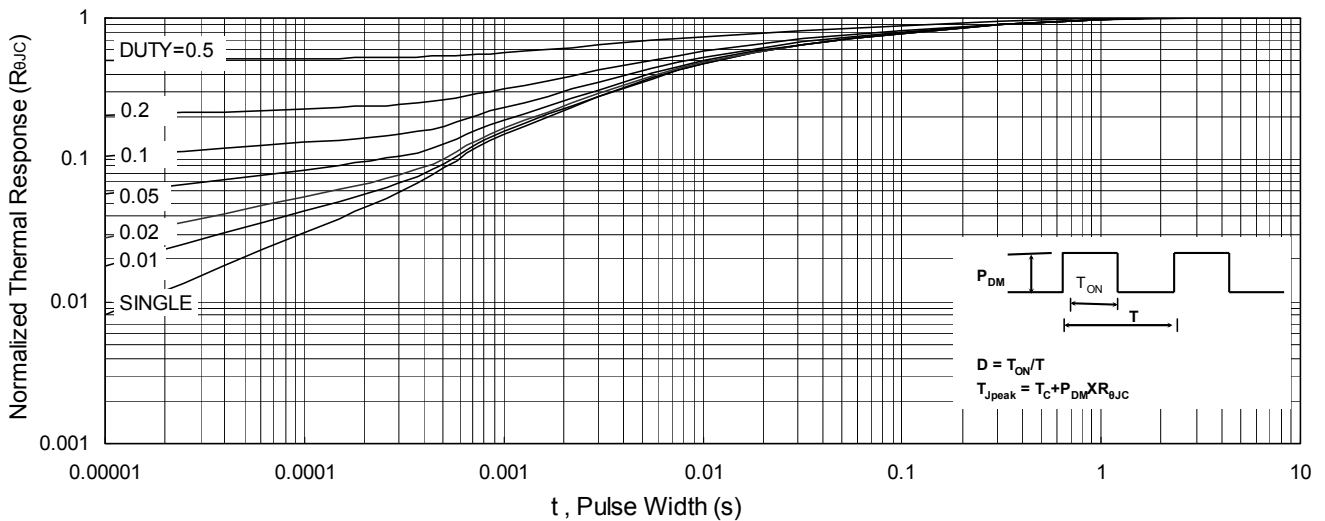


Fig.13 Normalized Maximum Transient Thermal Impedance

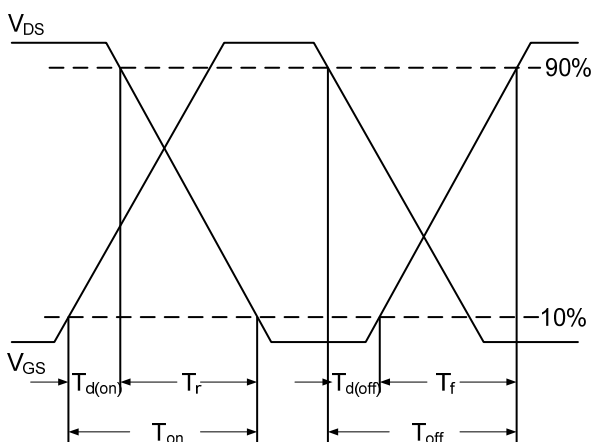


Fig.10 Switching Time Waveform

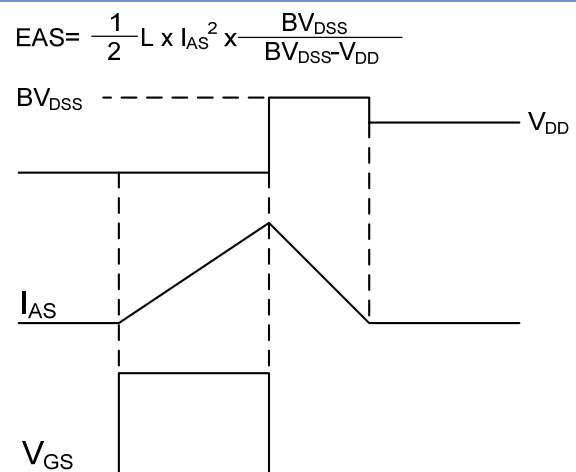


Fig.11 Unclamped Inductive Switching Waveform